Session V

Wireless Applications

Chairman:

C. Kermarrec
Analog Devices

Co-Chairman:

D. Lovelace
Motorola

The market for RF wireless applications has exploded in the last few years. Requirements for high performance, low power consumption, highly integrated, low cost RF components have challenged development and production engineers. Silicon BJT and GaAs HBT, MESFET and HFET technologies are competing to gain a substantial share of the wireless RF market. The wireless application session will present five papers addressing performances of 900 MHz silicon and GaAs HBT LNAs, GaAs HFET capability of producing ultra low power 900 MHz downconverters, performance of 800 MHz low cost GaAs MESFET upconverters using miniaturized capacitors and the development of highly integrated receiver based on micro bump handling technology.

1:30 p.m.–3:10 p.m., Monday, May 15, 1995
Room CC-A1